

**BYC100W-1200P** 

### Hyperfast power diode

Rev.01 - 10 January 2018

**Product data sheet** 

#### **1. General description**

EEPP<sup>™</sup>- Efficiency Enhanced Pt Planar rectifier in a TO247-2L plastic package.

#### 2. Features and benefits

- Fast switching
- · Reduces switching losses with improved lower reverse recovery charge
- Soft recovery characteristics
- Low thermal resistance
- Low leakage current
- Planar termination structure
- High operating temperature capability ( $T_{j (max)} = 175^{\circ}C$ )
- Higher I<sub>FSM</sub> capability

#### 3. Applications

- Switched-Mode Power Supplies
- Power factor correction diode
- Uninterrupted Power Supply

## 4. Quick reference data

#### Table 1. Quick reference data

| Symbol             | Parameter                              | Conditions   |     | Values |     | Unit |      |
|--------------------|--|--|-----|--------|-----|------|------|
| Absolute           | maximum rating                         |  |     |        |     |      |      |
| $V_{\text{RRM}}$   | repetitive peak reverse voltage        |  |     | 1200   |     | V    |      |
| I <sub>F(AV)</sub> | average forward current                | δ = 0.5 ; square-wave pulse; T <sub>mb</sub> ≤ 78 °C;<br>Fig. 1; Fig. 2; Fig. 3                                |     | 100    |     | A    |      |
| I <sub>FRM</sub>   | repetitive peak forward current        | δ = 0.5 ; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 78 °C;<br>square-wave pulse                                |     | 200    |     | A    |      |
| I <sub>FSM</sub>   | non-repetitive peak<br>forward current | $t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse;<br>Fig. 4   | 900 |        |     | A    |      |
|                    |  | $t_{\rm p}$ = 8.3 ms; $T_{\rm j(init)}$ = 25 °C; sine-wave pulse;  |     |        | А   |      |      |
| Symbol             | Parameter                              | Conditions   |     | Min    | Тур | Max  | Unit |
| Static ch          | aracteristics                          |  |     |        |     |      |      |
| V <sub>F</sub>     | forward voltage                        | I <sub>F</sub> = 100 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>  |     | -      | 2.8 | 3.3  | V    |
|                    |  | I <sub>F</sub> = 100 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>   |     | -      | 2.2 | -    | V    |
| Dynamic            | characteristics                        | ·  |     |        |     |      |      |
| t <sub>rr</sub>    | reverse recovery time                  | $I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$<br>$T_j = 25 \text{ °C}; Fig. 7$ |     | -      | -   | 90   | ns   |

# **5. Pinning information**

| Table 2. F | Pinning infor | mation                             |                    |                         |
|------------|---------------|------------------------------------|--------------------|-------------------------|
| Pin        | Symbol        | Description                        | Simplified outline | Graphic symbol          |
| 1          | К             | cathode                            |                    | K <u>A</u><br>001aaa020 |
| 2          | А             | anode                              |                    | 001888020               |
| mb         | mb            | mounting base; connected to cathod | K A<br>TO247-2L    |                         |

# 6. Ordering information

| Table 3. Ordering information |          |   |           |  |  |
|-------------------------------|----------|---|-----------|--|--|
| Type number                   | Package  |   |           |  |  |
|                               | Name     | Description   | Version   |  |  |
| BYC100W-1200P                 | TO247-2L | Plastic single-ended through-hole package; heatsink mounted;1 mounting hole; 2 leads TO-247 | TO247A-2L |  |  |

## 7. Marking

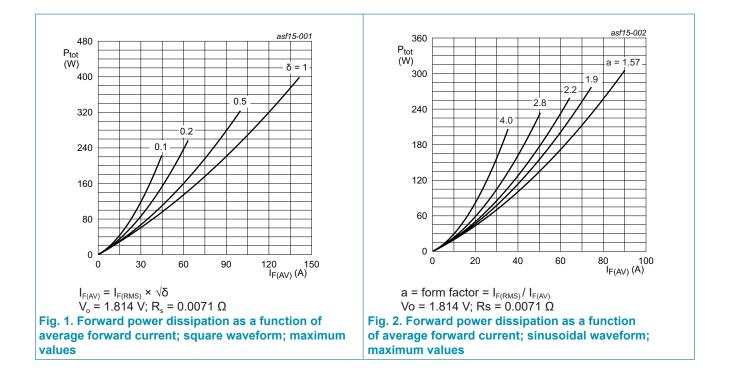
| Table 4. Marking codes |               |               |  |  |  |  |
|------------------------|---------------|---------------|--|--|--|--|
|                        | Type number   | Marking codes |  |  |  |  |
|                        | BYC100W-1200P | BYC100W-1200P |  |  |  |  |

## 8. Limiting values

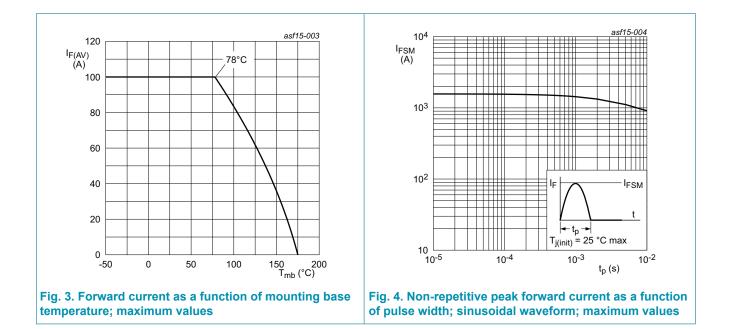
#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol             | Parameter                              | Conditions  | Values     | Unit |
|--------------------|--|---|------------|------|
| $V_{\text{RRM}}$   | repetitive peak reverse voltage        |   | 1200       | V    |
| V <sub>RWM</sub>   | crest working reverse voltage          |   | 1200       | V    |
| V <sub>R</sub>     | reverse voltage                        | DC  | 1200       | V    |
| I <sub>F(AV)</sub> | average forward current                | δ = 0.5 ; square-wave pulse; T <sub>mb</sub> ≤ 78 °C;<br>Fig. 1; Fig. 2; Fig. 3 | 100        | A    |
| I <sub>FRM</sub>   | repetitive peak forward current        | δ = 0.5; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 78 °C;<br>square-wave pulse  | 200        | A    |
| I <sub>FSM</sub>   | non-repetitive peak<br>forward current | $t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse;<br>Fig. 4                | 900        | A    |
|                    |  | $t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse;                         | 1000       | А    |
| T <sub>stg</sub>   | storage temperature                    |   | -65 to 175 | °C   |
| Tj                 | junction temperature                   |   | 175        | °C   |

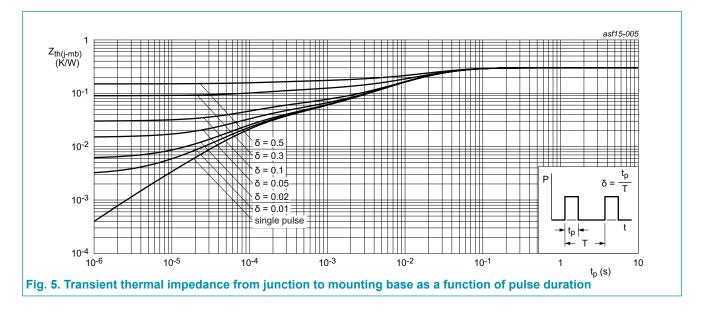


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## 9. Thermal characteristics

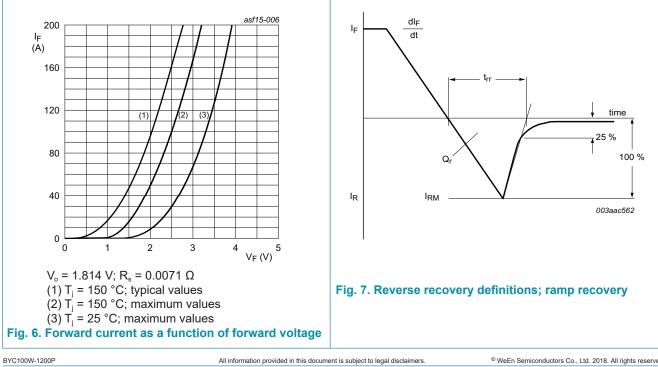
| Symbol                | Parameter  | Conditions    | Min | Тур | Max | Unit |
|-----------------------|--|---------------|-----|-----|-----|------|
| $R_{\text{th(j-mb)}}$ | thermal resistance<br>from junction to<br>mounting base    | <u>Fig. 5</u> | -   | -   | 0.3 | K/W  |
| $R_{\text{th(j-a)}}$  | thermal resistance<br>from junction to<br>ambient free air | in free air   | -   | 45  | -   | K/W  |



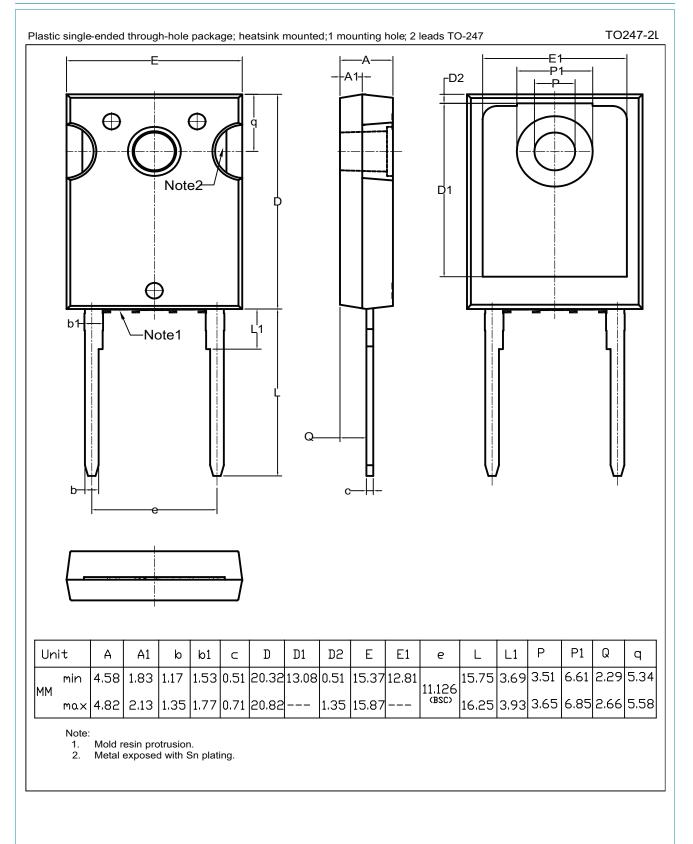
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### **10.** Characteristics

| able 7. Ch                     | naracteristics                   |  |   |      |     |      |
|--------------------------------|----------------------------------|--|---|------|-----|------|
| Symbol                         | Parameter                        | Conditions   | Min   | Тур  | Max | Unit |
| Static cha                     | racteristics                     |  |   |      |     |      |
| V <sub>F</sub> forward current | forward current                  | I <sub>F</sub> = 100 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>  | -   | 2.8  | 3.3 | V    |
|                                |                                  | I <sub>F</sub> = 100 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>   | -   | 2.2  | -   | V    |
| I <sub>R</sub>                 | reverse current                  | V <sub>R</sub> = 1200 V; T <sub>j</sub> = 25 °C  | -   | -    | 250 | μA   |
|                                |                                  | V <sub>R</sub> = 1200 V; T <sub>j</sub> = 150 °C   | -   | -    | 2   | mA   |
| Dynamic                        | characteristics                  |  |   |      |     |      |
| Q <sub>r</sub>                 | reverse charge                   | $I_F = 50 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$<br>$T_j = 25 \text{ °C}; Fig. 7$         | -   | 1330 | -   | nC   |
|                                |                                  | $I_F = 50 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$<br>$T_j = 125 \text{ °C}; Fig. 7$        | -   | 4540 | -   | nC   |
|                                |                                  | $I_F = 50 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$<br>$T_j = 150 \text{ °C}; Fig. 7$        | -   | 5425 | -   | nC   |
| t <sub>rr</sub> reve           | reverse recovery time            | $I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$<br>$T_j = 25 \text{ °C}; Fig. 7$           | -   | -    | 90  | ns   |
|                                |                                  | $I_F = 50 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$<br>$T_j = 25 \text{ °C}; Fig. 7$         | -   | 115  | -   | ns   |
|                                |                                  | $I_F = 50 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$<br>T <sub>j</sub> = 125 °C; Fig. 7       | -   | 244  | -   | ns   |
|                                |                                  |  | $I_F = 50 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$<br>$T_j = 150 \text{ °C}; Fig. 7$ | -    | 276 | -    |
| I <sub>RM</sub>                | peak reverse recovery<br>current | $I_F = 50 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$<br>$T_j = 25 \text{ °C}; Fig. 7$         | -   | 22.9 | -   | A    |
|                                |                                  | $I_F = 50 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$<br>$T_j = 125 \text{ °C}; Fig. 7$        | -   | 37.0 | -   | A    |
|                                |                                  | I <sub>F</sub> = 50 A; V <sub>R</sub> = 400 V; dI <sub>F</sub> /dt = 500 A/μs;<br>T <sub>i</sub> = 150 °C; <u>Fig. 7</u> | -   | 39.2 | -   | A    |



## **11. Package outline**



# BYC100W-1200P

#### Hyperfast power diode

## 12. Legal information

#### Data sheet status

| Document status [1][2]               | Product<br>status [3] | Definition  |
|--------------------------------------|-----------------------|---|
| Objective<br>[short] data<br>sheet   | Development           | This document contains data from<br>the objective specification for product<br>development. |
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